

SANYO

No.4647

2SK1896

N-Channel MOS Silicon FET

DC-DC Converter,
Motor Drive Applications**Features**

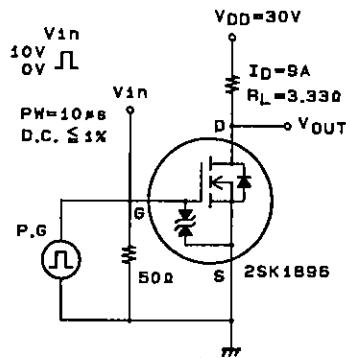
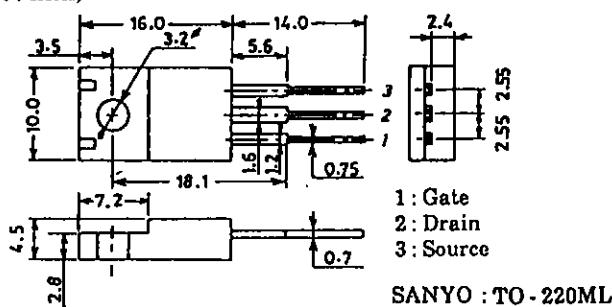
- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating easy mounting.

Absolute Maximum Ratings at Ta = 25°C

			unit
Drain-to-Source Voltage	V _{DSS}	60	V
Gate-to-Source Voltage	V _{GSS}	±20	V
Drain Current(DC)	I _D	15	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10 μs, duty cycle ≤ 1% 60	A
Allowable Power Dissipation	P _D	2.0	W
		T _c = 25°C	25 W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

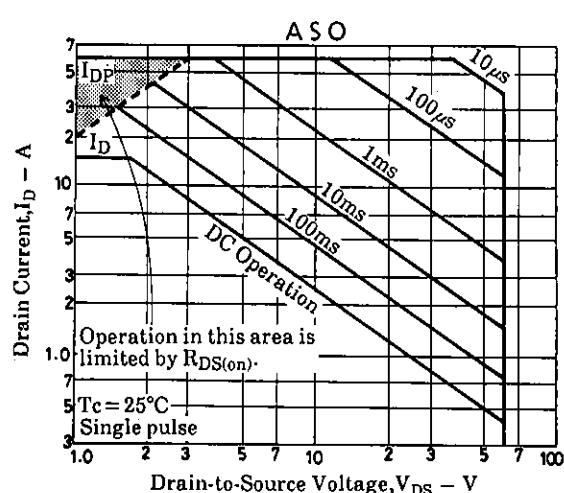
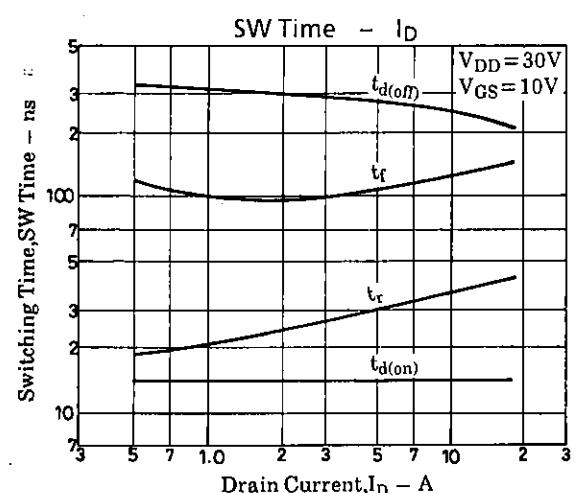
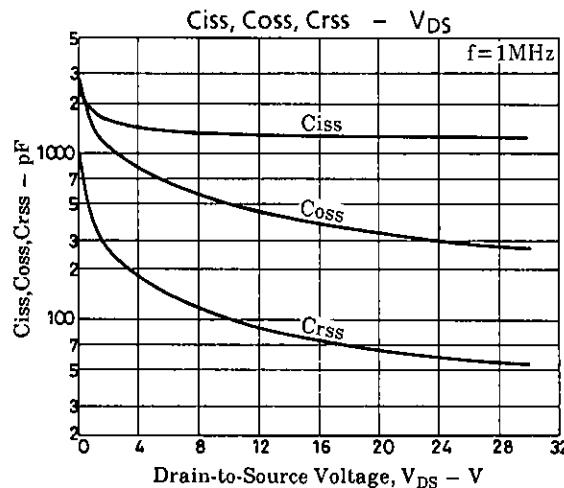
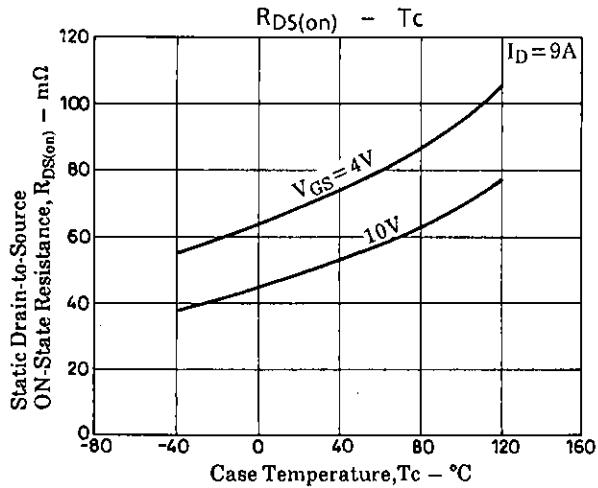
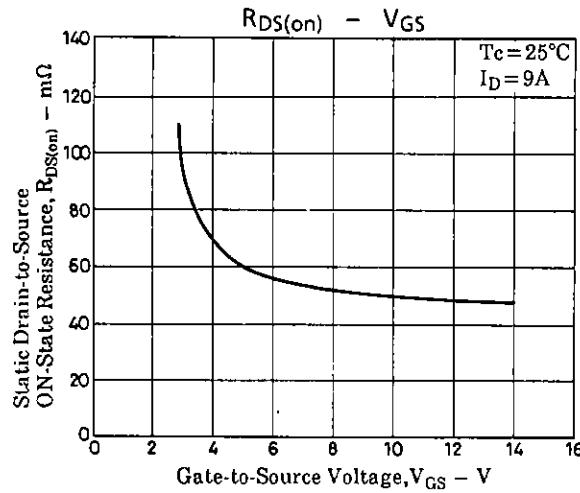
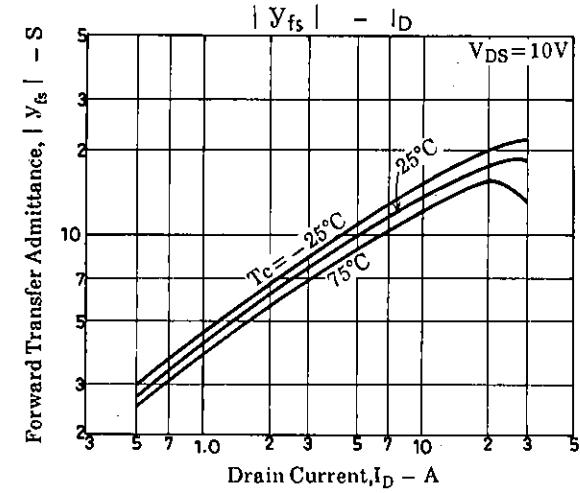
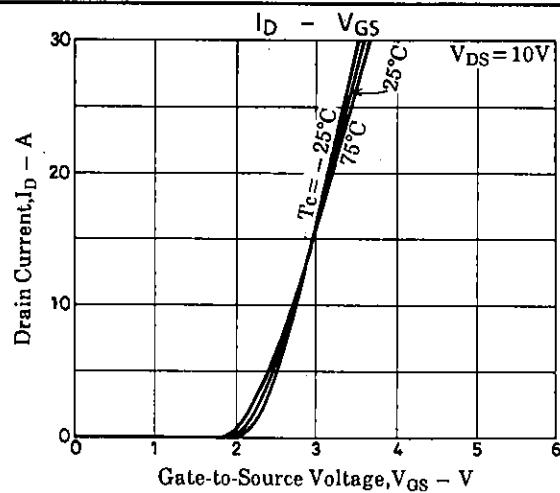
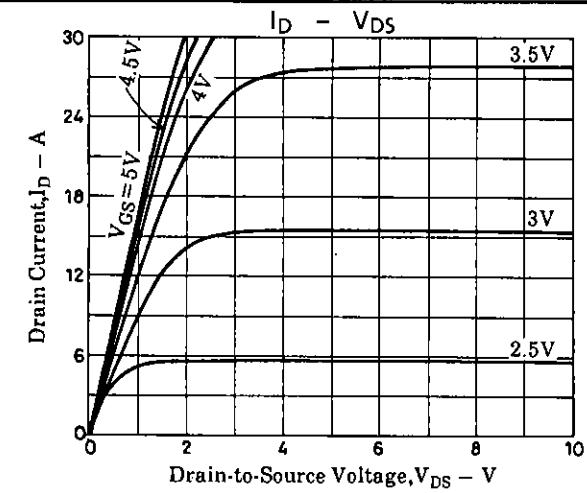
Electrical Characteristics at Ta = 25°C

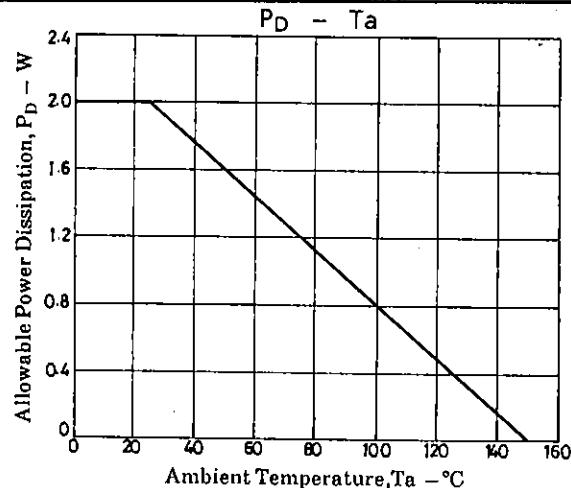
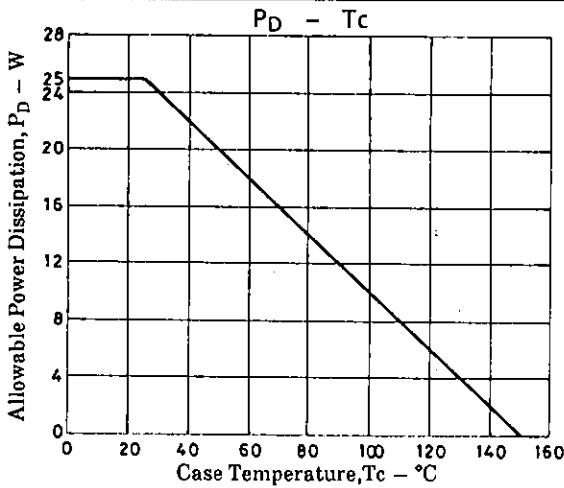
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = 1mA, V _{GS} = 0	60			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ± 100 μA, V _{DS} = 0	±20			V
Zero-Gate Voltage	I _{DSS}	V _{DS} = 60V, V _{GS} = 0			100	μA
Drain Current						
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ± 16V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = 10V, I _D = 1mA	1.0		2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = 10V, I _D = 9A	8	13		S
Static Drain-to-Source	R _{DS(on)}	I _D = 9A, V _{GS} = 10V	0.05	0.07		Ω
ON-State Resistance	R _{DS(on)}	I _D = 9A, V _{GS} = 4V	0.07	0.095		Ω
Input Capacitance	C _{iss}	V _{DS} = 20V, f = 1MHz	1230			pF
Output Capacitance	C _{oss}	V _{DS} = 20V, f = 1MHz	330			pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = 20V, f = 1MHz	65			pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.	14			ns
Rise Time	t _r	"	35			ns
Turn-OFF Delay Time	t _{d(off)}	"	250			ns
Fall Time	t _f	"	120			ns
Diode Forward Voltage	V _{SD}	I _S = 15A, V _{GS} = 0	1.0	1.5		V

Switching Time Test Circuit**Package Dimensions 2063A**
(unit : mm)

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